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P12663*Amendments***In the Specification**

Please replace paragraph [0001] with the following amended paragraph:

[0001] ~~The present invention~~ Embodiments generally relates to space transformers and to methods of manufacturing space transformers.

In the Claims:

The claims are to be amended as follows:

1-9. (Previously Cancelled).

10-15. (Cancelled)

16-17. (Previously cancelled)

18. (Currently amended) A test card assembly comprising:

a test card printed circuit board having first contacts thereon;

a probe head having second contacts thereon; and

a space transformer comprising:

a silicon medium having a land grid array side and a semiconductor side opposite the land grid array side; and

a predetermined contact pattern comprising electrically conductive material disposed in an inner region of the silicon medium and defining electrical contact zones providing double-sided electrical contacts for the space transformer, the contacts comprising:

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land grid array side contacts disposed on the land grid array side of the silicon medium and having their largest dimension and their pitch in the order of mils to define a macro-pitch scale, the land grid array side contacts further being adapted to be connected to corresponding ones of the first contacts; and

semiconductor side contacts disposed on the semiconductor side of the silicon medium and having their largest dimension and their pitch in the order of microns to define a micro-pitch scale, the semiconductor side contacts further being adapted to be connected to corresponding ones of the second contacts, the electrical contact zones further being disposed to convert a macro-pitch scale of the land grid array side contacts to the micro-pitch scale of the semiconductor side contacts.

19. (Previously presented) The assembly according to claim 18, wherein the silicon medium comprises a first silicon layer and a second silicon layer, the contact pattern being disposed between the first silicon layer and the second silicon layer.

20. (New) The space transformer according to claim 18, wherein the second silicon layer defines at least one via therein, at least some of the electrically conductive material being located in the at least one via.

21. (New) The space transformer according to claim 18, further comprising an adhesion promoter disposed between the electrically conductive material and the first silicon layer.